

Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.8)	V_{pp}	2.5	kV
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ELECTRICAL CHARACTERISTICS (unless otherwise specified)

Symbol	Test Condition	Quadrant	Value	Unit	
I	$V_D=12V R_L=33$	- -	MAX.	50	mA
V		- -	MAX.	1.3	V
V	$V_D=V_{DRM} T_j=125$ $R_L=3.3k$	- -	MIN.	0.15	V
I _L	$I_G=1.2I_{GT}$	-	MAX.	80	mA
				100	
I _H	$I_T=500mA$		MAX.	75	mA
dV/dt	$V_D=540V$ Gate Open $T_j=125$		MIN.	2000	V/s
(dI/dt) _c	$I_G=90mA$ $I_A=90mA$ $I_R=40mA$ $T_j=125$		MIN.	25	A/ms
t _{on}	$I_G=80mA$ $I_A=400mA$ $I_R=40mA$ $T_j=25$		TYP.	10	s
t _{off}				70	

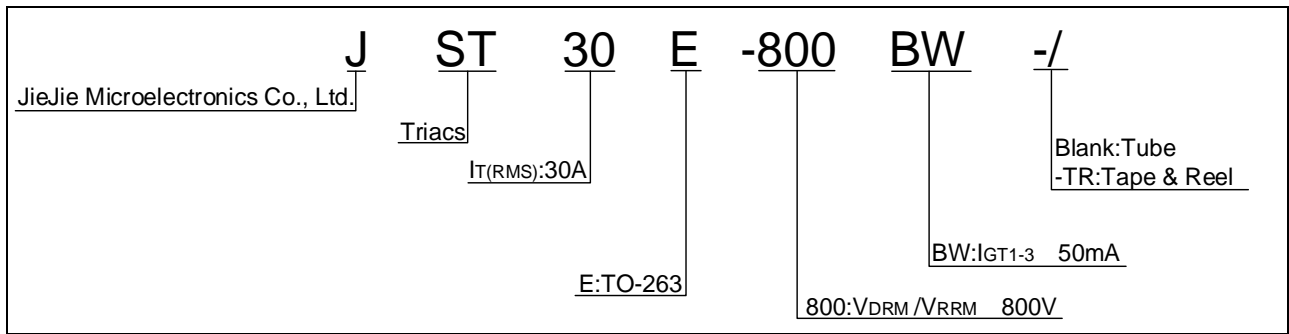
STATIC CHARACTERISTICS

Symbol	Parameter	Value(MAX.)	Unit	
V _{TM}	$I_{TM}=42A$ $t_p=380$ s $T_j=25$	1.5	V	
V _{TO}	Threshold voltage $T_j=125$	0.72	V	
R _D	Dynamic resistance $T_j=125$	25	m	
I _{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25$	5	A
I _{RPM}		$T_j=125$	2	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th(j-c)}	junction to case (AC)	0.7	°C/W
R _{th(j-a)}	junction to ambient (AC, in free air, S=2cm ²)	45	°C/W

ORDERING INFORMATION



MARKING

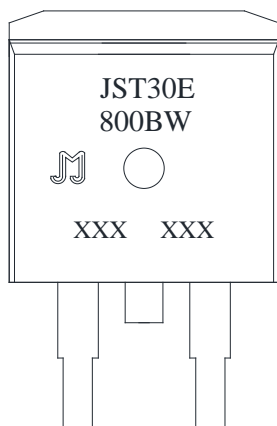


FIG.1: Maximum power dissipation versus RMS on-state current

FIG.2: RMS on-state current versus case temperature

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

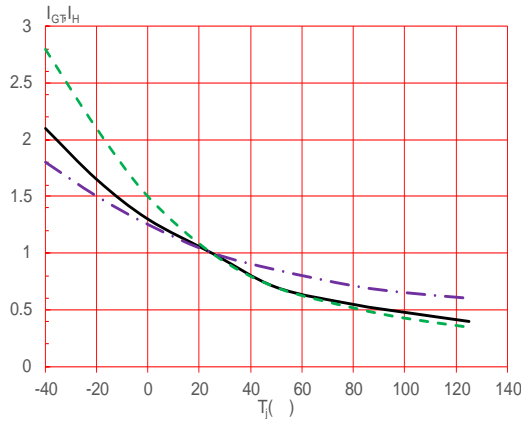
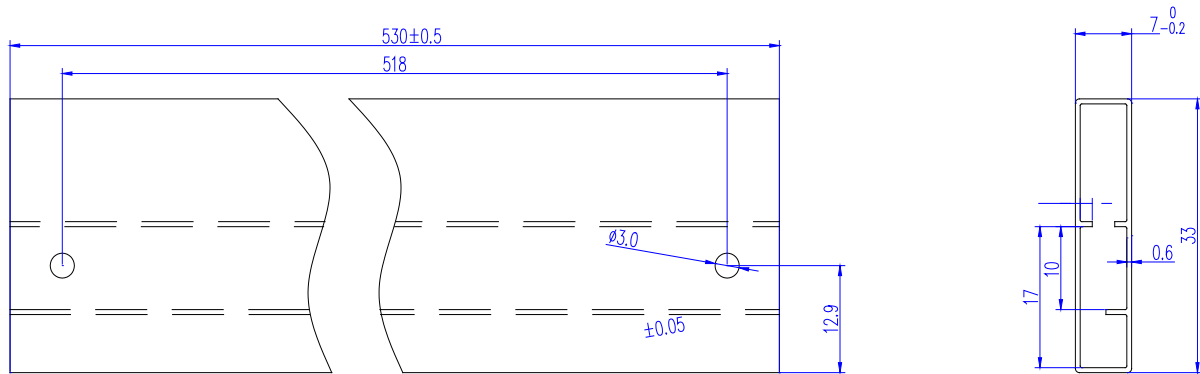


FIG.8: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



DELIVERY MODE



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